## N-Channel 100-V (D-S) MOSFET

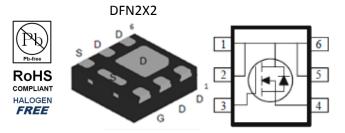
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>□</sub> (A)	
100	92 @ V <sub>GS</sub> = 10V	4.7	
	99 @ V <sub>GS</sub> = 4.5V	4.5	



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage	$V_{DS}$	100	V			
Gate-Source Voltage		$V_{GS}$	±20	٧		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I <sub>D</sub>	4.7			
Continuous Drain Current	T <sub>A</sub> =70°C		3.8	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	20			
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	4	Α		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3	W		
Power Dissipation	T <sub>A</sub> =70°C	'D	1.9	V V		
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	40	°C/W		
IMAXIMUM Sunction-to-Ambient	Steady State	ГХ⊕ЈА	90			

1

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

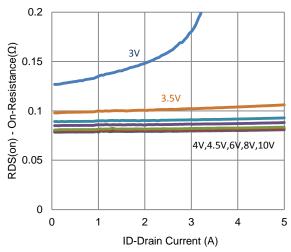
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	7			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_D = 3.7 \text{ A}$			92	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 3 \text{ A}$			99	11122	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 3.7 \text{ A}$		10		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		10			
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 3.7 \text{ A}$		3.6		nC	
Gate-Drain Charge	$Q_gd$	1 <sub>D</sub> = 3.7 A		3.5			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 50 \text{ V}, R_1 = 13.6 \Omega,$		6			
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_L - 15.0 \Omega,$ $I_D = 3.7 \text{ A},$		6		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		34		ns	
Fall Time	t <sub>f</sub>	V GEN = 10 V, 1 (GEN = 0.12		8			
Input Capacitance	C <sub>iss</sub>			1607			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		66		pF	
Reverse Transfer Capacitance	$C_{rss}$			46			

#### Notes

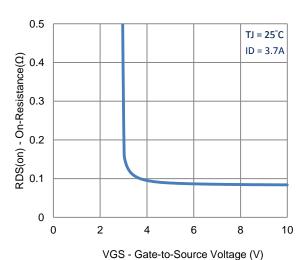
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

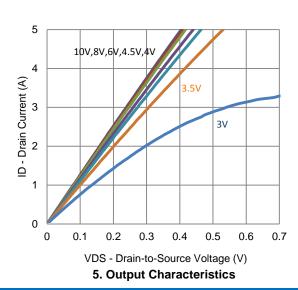
### **Typical Electrical Characteristics**

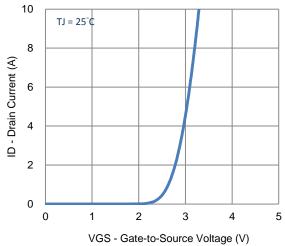


#### 1. On-Resistance vs. Drain Current

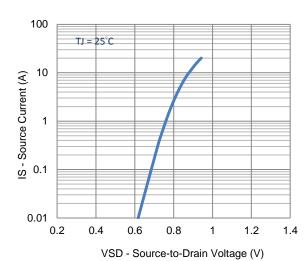


3. On-Resistance vs. Gate-to-Source Voltage

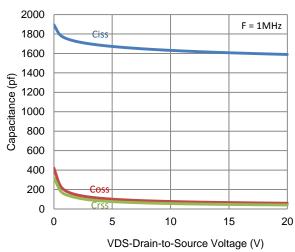




2. Transfer Characteristics

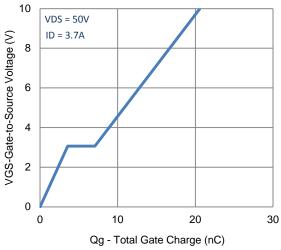


4. Drain-to-Source Forward Voltage

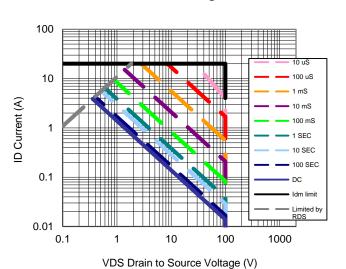


6. Capacitance

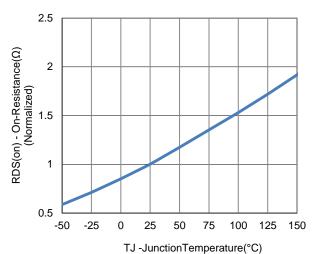
### **Typical Electrical Characteristics**



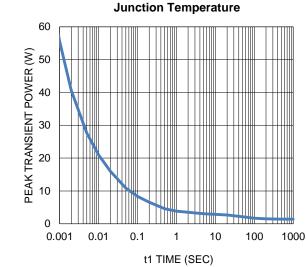
7. Gate Charge



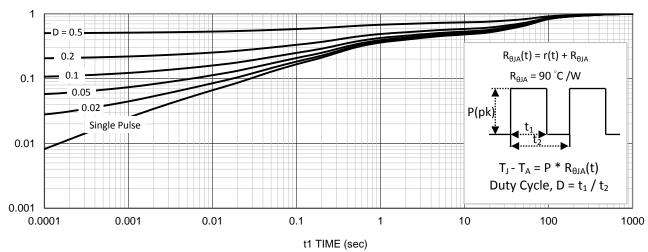
9. Safe Operating Area



8. Normalized On-Resistance Vs

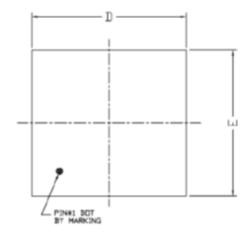


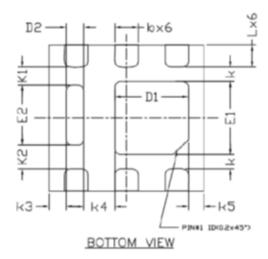
10. Single Pulse Maximum Power Dissipation

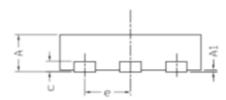


11. Normalized Thermal Transient Junction to Ambient

# Package Information







	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0, 50	0, 55	0.60	0, 020	0.022	0.024	
A1	0.00		0.05	0.000		0.002	
ъ	0.25	0.30	0.35	0.010	0.012	0.014	
С	0. 152 REF				0.006 REF		
D	1.90	2.00	2. 10	0.075	0.079	0.083	
D1	0.85	0.95	1.05	0.033	0.037	0.041	
D2	0.13	0.23	0.33	0.005	0.009	0.013	
E	1.90	2.00	2.10	0.075	0.079	0.083	
E1	0.90	1.00	1.10	0.035	0.039	0.043	
E2	0.72	0.82	0.92	0.028	0.032	0.036	
c	0.65 BSC			0. 026 BSC			
K	0, 20 BSC			0.008 BSC			
K1	0, 25 BSC			0, 010 BSC			
K2	0. 33 BSC			0.013 BSC			
K3	0. 22 BSC			0.009 BSC			
K4	0.40 BSC			0.016 BSC			
K5		0.20 BSC			0.008 BSC		
L	0, 25	0.30	0.35	0,010	0,012	0.014	